



**THE DATASHEET OF  
SQM120P10\_10M1LGE3**





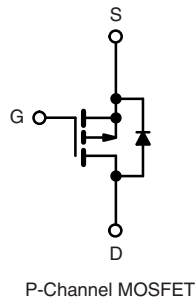
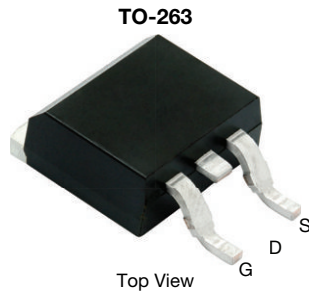
# Automotive P-Channel 100 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	-100
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = -10 V	0.0101
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = -4.5 V	0.0150
I <sub>D</sub> (A)	-120
Configuration	Single
Package	TO-263

### FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R<sub>g</sub> and UIS tested
- AEC-Q101 qualified
- Material categorization:  
for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	-100	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current <sup>a</sup>	I <sub>D</sub>	T <sub>C</sub> = 25 °C <sup>a</sup>	-120
		T <sub>C</sub> = 125 °C	-78
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	-120	A
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	-480	
Single Pulse Avalanche Current	I <sub>AS</sub>	-78	
Single Pulse Avalanche Energy	E <sub>AS</sub>	304	mJ
Maximum Power Dissipation <sup>b</sup>	P <sub>D</sub>	T <sub>C</sub> = 25 °C	
		T <sub>C</sub> = 125 °C	125
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R <sub>thJA</sub>	40	°C/W
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.4	

#### Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).



SPECIFICATIONS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = -250\text{ }\mu\text{A}$	-100	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\text{ }\mu\text{A}$	-1.5	-2.0	-2.5	
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = -100\text{ V}$	-	-	-1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = -100\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	-50	
		$V_{GS} = 0\text{ V}$ , $V_{DS} = -100\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$	-	-	-500	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{GS} = -10\text{ V}$ , $V_{DS} \leq -5\text{ V}$	-120	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$ , $I_D = -30\text{ A}$	-	0.0081	0.0101	$\Omega$
		$V_{GS} = -10\text{ V}$ , $I_D = -30\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	0.0168	
		$V_{GS} = -10\text{ V}$ , $I_D = -30\text{ A}$ , $T_J = 175\text{ }^\circ\text{C}$	-	-	0.0205	
		$V_{GS} = -4.5\text{ V}$ , $I_D = -20\text{ A}$	-	0.0114	0.0150	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = -15\text{ V}$ , $I_D = -25\text{ A}$	-	60	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = -25\text{ V}$ , $f = 1\text{ MHz}$	-	6750	9000	$\mu\text{F}$
Output Capacitance	$C_{oss}$		-	3500	5000	
Reverse Transfer Capacitance	$C_{rss}$		-	450	600	
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{GS} = -10\text{ V}$ , $V_{DS} = -50\text{ V}$ , $I_D = -70\text{ A}$	-	125	190	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$		-	25	-	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	30	-	
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	3	6.44	9.7	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = -50\text{ V}$ , $R_L = 0.71\text{ }\Omega$ $I_D \cong -70\text{ A}$ , $V_{GEN} = -10\text{ V}$ , $R_g = 1\text{ }\Omega$	-	20	30	ns
Rise Time <sup>c</sup>	$t_r$		-	100	150	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$		-	120	180	
Fall Time <sup>c</sup>	$t_f$		-	200	300	
<b>Source-Drain Diode Ratings and Characteristics <sup>b</sup></b>						
Pulsed Current <sup>a</sup>	$I_{SM}$		-	-	-480	A
Forward Voltage	$V_{SD}$	$I_F = -100\text{ A}$ , $V_{GS} = 0\text{ V}$	-	-0.95	-1.5	V
Reverse Recovery Time <sup>b</sup>	$t_{rr}$	$V_R = -80\text{ V}$ , $I_F = -50\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	-	110	-	ns
Reverse Recovery Charge <sup>b</sup>	$Q_{rr}$		-	385	-	nC

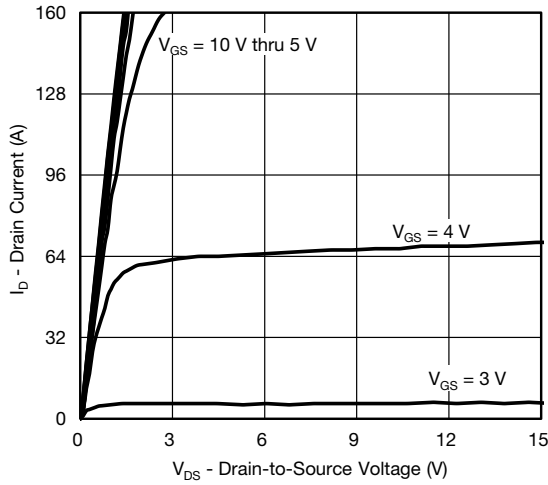
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.  
c. Independent of operating temperature.

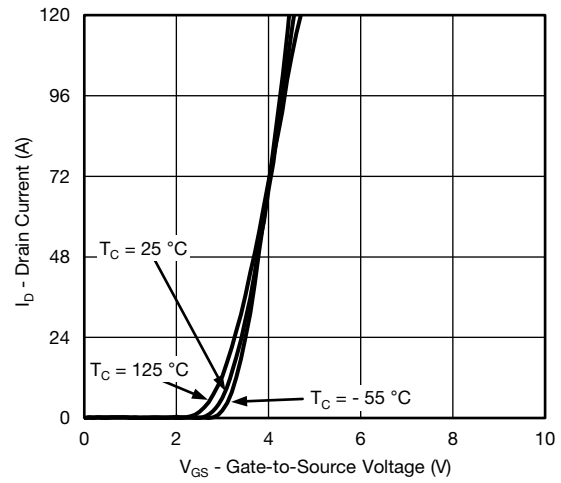
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



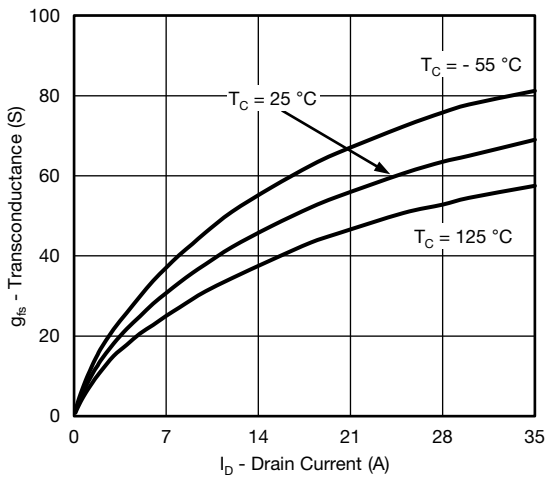
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



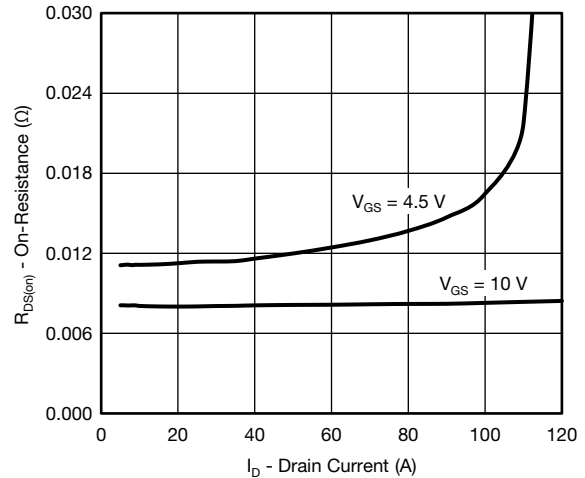
Output Characteristics



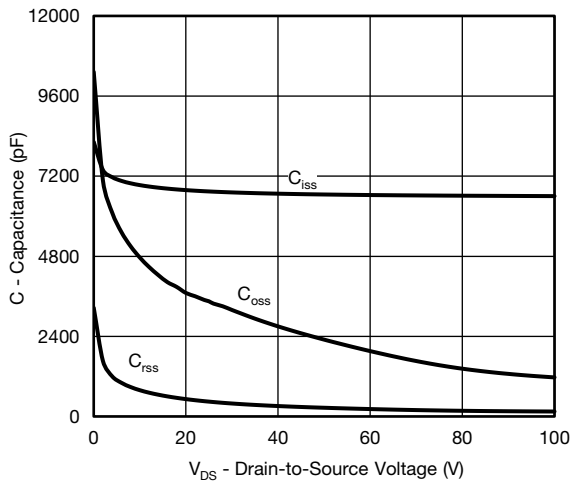
Transfer Characteristics



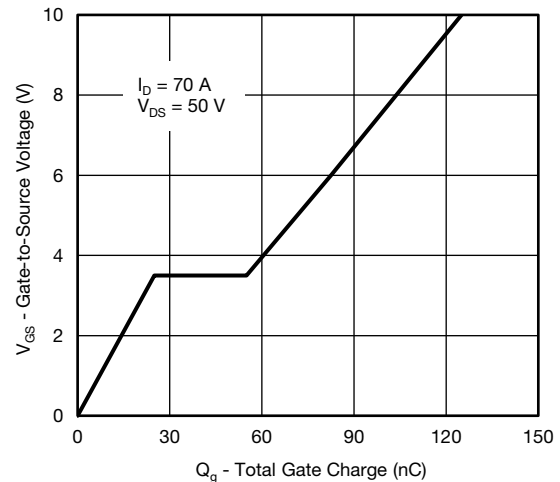
Transconductance



On-Resistance vs. Drain Current



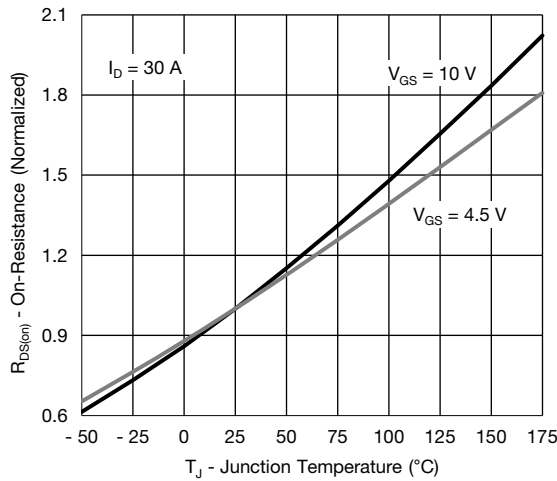
Capacitance



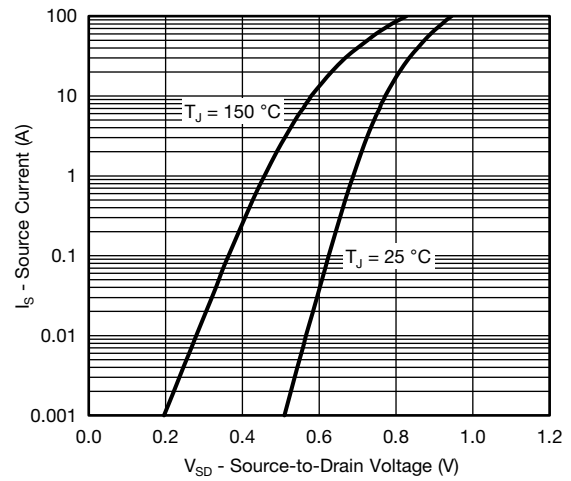
Gate Charge



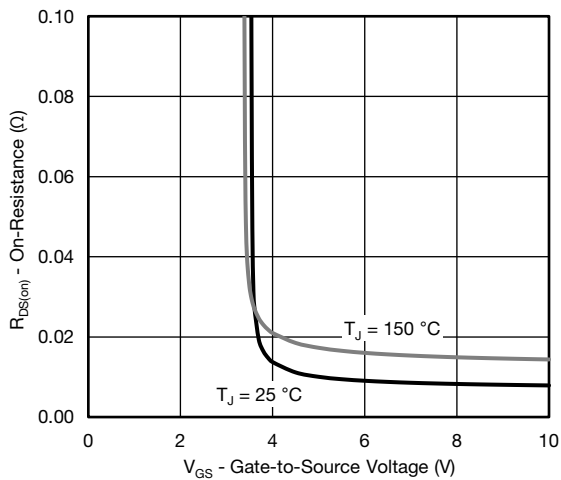
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



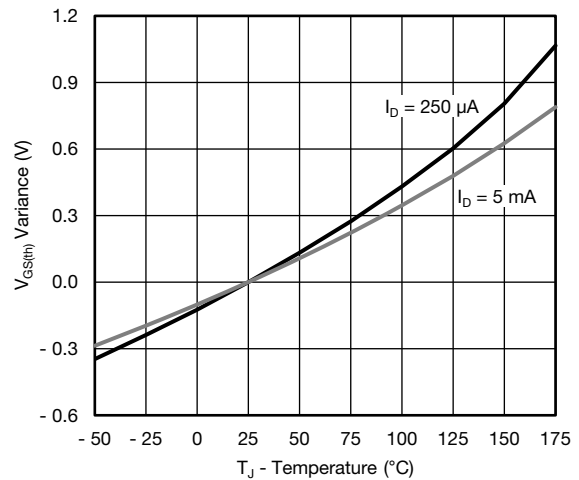
**On-Resistance vs. Junction Temperature**



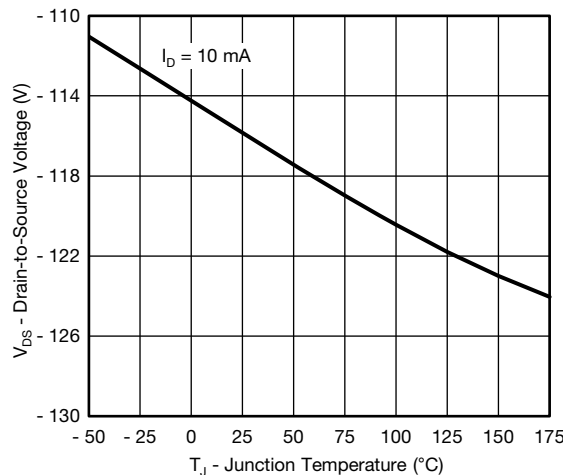
**Source Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



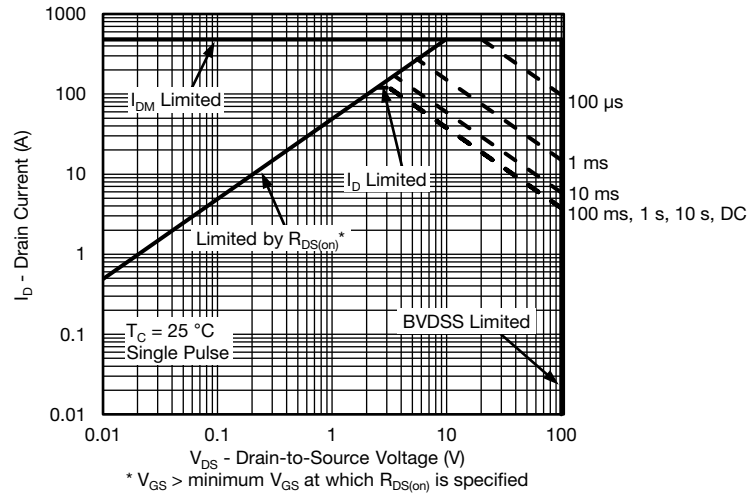
**Threshold Voltage**



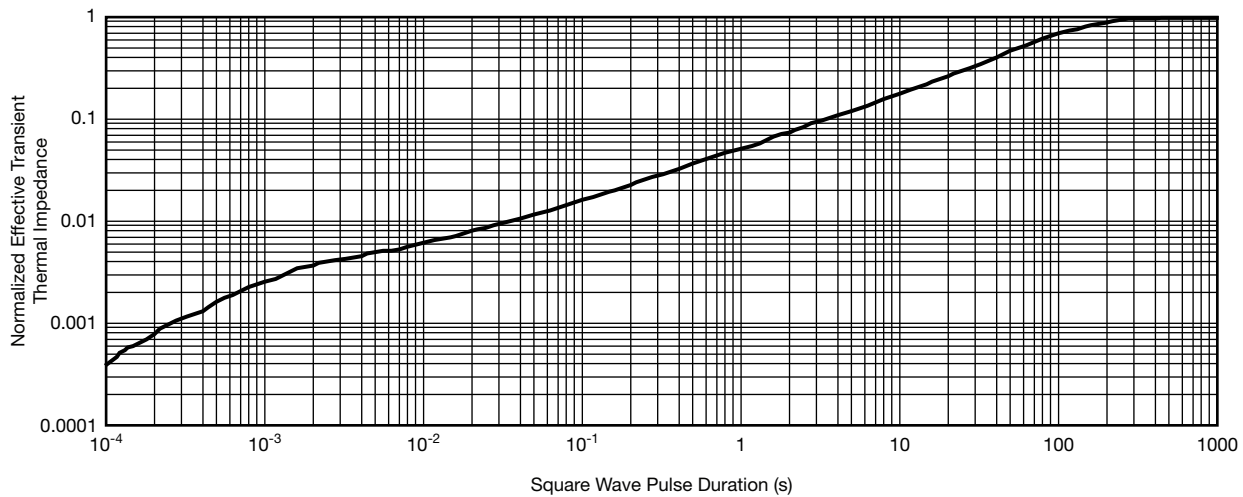
**Drain Source Breakdown vs. Junction Temperature**



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



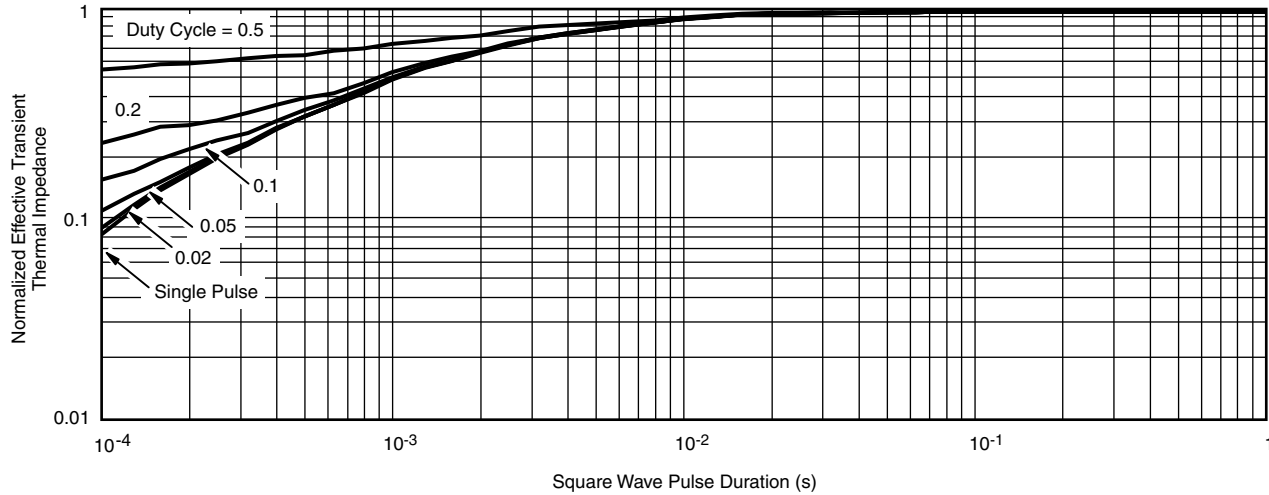
**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**

- The characteristics shown in the two graphs
    - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
    - Normalized Transient Thermal Impedance Junction to Case (25 °C)
- are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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# TO-263 (D<sup>2</sup>PAK): 3-LEAD



DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

**Notes**

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- \*: Thin lead is for SUB, SYB.  
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
- This feature is for thick lead.

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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